

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application:

#### **Listing of Claims:**

Claims 1-11 (Canceled)

Claim 12 (Currently Amended): A semiconductor device, comprising:

a semiconductor element having a first surface and a second surface, the first surface being an opposite surface with respect to the second surface of the semiconductor element;

an electrode formed at the first surface of the semiconductor element;

a wiring portion formed on the first surface of the semiconductor element and connected to the electrode;

a conductive post formed on the first surface of the semiconductor element and connected to the wiring portion;

a resin layer formed on the first surface of the semiconductor element so as to cover the first surface of the semiconductor element, the wiring portion and a side of the conductive post;

an external connection formed on the conductive post; and

a protective layer formed on the second surface of the semiconductor element,

wherein an end portion of the protective layer is aligned with both an end portion of the semiconductor element and an end portion of the resin layer, and wherein the end portions of the protective layer, the semiconductor element and the resin layer define an outer edge of the semiconductor device.

Claim 13 (Previously Presented): A semiconductor device according to claim 12, wherein the protective layer is a tape comprised of a hardened synthetic resin achieving a bonding function.

Claim 14 (Previously Presented): A semiconductor device according to claim 12, wherein the protective layer comprises a polyimide or an epoxy resin.

Claim 15 (Previously Presented): A semiconductor device according to claim 12, wherein the external connection is a solder ball.

Claim 16 (Previously Presented): A semiconductor device according to claim 12, wherein the conductive post is comprised of copper.

Claim 17 (Currently Amended): A semiconductor device, comprising:

a semiconductor element having a first surface and a second surface, the first surface being an opposite surface with respect to the second surface of the

semiconductor element;

an electrode formed at the first surface of the semiconductor element;

a wiring portion formed on the first surface of the semiconductor element and connected to the electrode;

a conductive post formed on the first surface of the semiconductor element and connected to the wiring portion;

a resin layer formed on the first surface of the semiconductor element so as to cover the first surface of the semiconductor element, the wiring portion and a side of the conductive post;

an external connection formed on the conductive post; and

a protective layer formed on the second surface of the semiconductor element, wherein a side surface of the semiconductor element is exposed from the resin layer and the protective layer, and wherein an end portion of the protective layer is aligned with both the exposed side surface of the semiconductor element and an end portion of the resin layer, and wherein the end portions of the protective layer and the resin layer, and the exposed side surface of the semiconductor element define an outer edge of the semiconductor device.

Claim 18 (Previously Presented): A semiconductor device according to claim 17, wherein the protective layer is a tape which comprises a hardened synthetic resin achieving a bonding function.

Claim 19 (Previously Presented): A semiconductor device according to claim 17,  
wherein the protective layer comprises a polyimide or an epoxy resin.

Claim 20 (Previously Presented): A semiconductor device according to claim 17,  
wherein the external connection is a solder ball.

Claim 21 (Previously Presented): A semiconductor device according to claim 17,  
wherein the conductive post is comprised of copper.

Claim 22 (Currently Amended): A semiconductor device, comprising:

- a semiconductor element having a first surface and a second surface, the first surface being an opposite surface with respect to the second surface of the semiconductor element;

- an electrode formed at the first surface of the semiconductor element;

- a wiring portion formed on the first surface of the semiconductor element and connected to the electrode;

- a conductive post having a first end portion and a second end portion, and being formed on the first surface of the semiconductor element, the first end portion of the conductive post being connected to the wiring portion;

- a resin layer formed on the first surface of the semiconductor element so as to cover the first surface of the semiconductor element, the wiring portion and a side of the

conductive post, the second end portion of the conductive post not being covered by the resin layer;

an external connection formed on the second end portion of the conductive post;  
and

a protective layer formed on the second surface of the semiconductor element, wherein only a side surface of the semiconductor element is exposed from the resin layer and the protective layer, [[and]] wherein an end portion of the protective layer is aligned with both the side surface of the semiconductor element and an end portion of the resin layer, and wherein the end portions of the protective layer and the resin layer, and the side surface of the semiconductor element define an outer edge of the semiconductor device.

Claim 23 (Previously Presented): A semiconductor device according to claim 22, wherein the protective layer is a tape which comprises a hardened synthetic resin achieving a bonding function.

Claim 24 (Previously Presented): A semiconductor device according to claim 22, wherein the protective layer comprises a polyimide or an epoxy resin.

Claim 25 (Previously Presented): A semiconductor device according to claim 22, wherein the external connection is a solder ball.

Claim 26 (Previously Presented): A semiconductor device according to claim 22, wherein the conductive post is comprised of copper.

Claim 27 (Currently Amended): A semiconductor device, comprising:

a semiconductor element having a first surface and a second surface, the first surface being an opposite surface with respect to the second surface of the semiconductor element;

an electrode formed at the first surface of the semiconductor element;

a wiring portion formed on the first surface of the semiconductor element and connected to the electrode;

a conductive post formed on the first surface of the semiconductor element and connected to the wiring portion;

a resin layer formed on the first surface of the semiconductor element so as to cover the first surface of the semiconductor element, the wiring portion and a side of the conductive post;

an external connection terminal formed on the conductive post; and

a protective layer formed on the second surface of the semiconductor element,

wherein a side surface of the protective layer is in a same plane with both a side surface of the semiconductor element and a side surface of the resin layer, and wherein the side surfaces of the protective layer, the semiconductor element and the resin layer

define an outer edge of the semiconductor device.

Claim 28 (Previously Presented): A semiconductor device according to claim 27, wherein the protective layer is a tape comprised of a hardened synthetic resin achieving a bonding function.

Claim 29 (Previously Presented): A semiconductor device according to claim 27, wherein the protective layer comprises a polyimide or an epoxy resin.

Claim 30 (Previously Presented): A semiconductor device according to claim 27, wherein the external connection terminal is a solder ball.

Claim 31 (Previously Presented): A semiconductor device according to claim 27, wherein the conductive post is comprised of copper.